



#### **ATP214-TL-H Information**



For Reference Only

Part Number ATP214-TL-H
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 60V 75A ATPAK

Package ATPAK (2 leads+tab)

For the pricing/inventory/lead time, please contact

us

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# **Certified Quality**

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## **ATP214-TL-H Specifications**

Manufacturer Part NumberATP214-TL-HManufacturerON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageATPAK (2 leads+tab)Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C75A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs96nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4850pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs8.1 mOhm @ 38A, 10VOperating Temperature150°C (TJ)		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  ATPAK (2 leads+tab)  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.1 mOhm @ 38A, 10V	Manufacturer Part Number	ATP214-TL-H
Package         ATPAK (2 leads+tab)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         75A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4V, 10V           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         96nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4850pF @ 20V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         60W (Tc)           Rds On (Max) @ Id, Vgs         8.1 mOhm @ 38A, 10V	Manufacturer	ON Semiconductor
Package ATPAK (2 leads+tab)  Series - FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 60V  Current - Continuous Drain (Id) @ 25°C 75A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 4V, 10V  Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 96nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 4850pF @ 20V  Vgs (Max) ±20V  FET Feature - Power Dissipation (Max) 60W (Tc)  Rds On (Max) @ Id, Vgs 8.1 mOhm @ 38A, 10V	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         75A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4V, 10V           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         96nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4850pF @ 20V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         60W (Tc)           Rds On (Max) @ Id, Vgs         8.1 mOhm @ 38A, 10V		Transistors - FETs, MOSFETs - Single
FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  75A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.1 mOhm @ 38A, 10V	Package	ATPAK (2 leads+tab)
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  75A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  MOSFET (Metal Oxide)  60V  75A (Ta)	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  75A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  60V  75A (Ta)  4V, 10V  4V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C       75A (Ta)         Drive Voltage (Max Rds On, Min Rds On)       4V, 10V         Vgs(th) (Max) @ Id       -         Gate Charge (Qg) (Max) @ Vgs       96nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       4850pF @ 20V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       60W (Tc)         Rds On (Max) @ Id, Vgs       8.1 mOhm @ 38A, 10V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)       4V, 10V         Vgs(th) (Max) @ Id       -         Gate Charge (Qg) (Max) @ Vgs       96nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       4850pF @ 20V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       60W (Tc)         Rds On (Max) @ Id, Vgs       8.1 mOhm @ 38A, 10V	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id       -         Gate Charge (Qg) (Max) @ Vgs       96nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       4850pF @ 20V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       60W (Tc)         Rds On (Max) @ Id, Vgs       8.1 mOhm @ 38A, 10V	Current - Continuous Drain (Id) @ 25°C	75A (Ta)
Gate Charge (Qg) (Max) @ Vgs       96nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       4850pF @ 20V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       60W (Tc)         Rds On (Max) @ Id, Vgs       8.1 mOhm @ 38A, 10V	Drive Voltage (Max Rds On, Min Rds On)	4V, 10V
Input Capacitance (Ciss) (Max) @ Vds	Vgs(th) (Max) @ Id	-
Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         60W (Tc)           Rds On (Max) @ Id, Vgs         8.1 mOhm @ 38A, 10V	Gate Charge (Qg) (Max) @ Vgs	96nC @ 10V
FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 8.1 mOhm @ 38A, 10V	Input Capacitance (Ciss) (Max) @ Vds	4850pF @ 20V
Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 8.1 mOhm @ 38A, 10V	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 8.1 mOhm @ 38A, 10V	FET Feature	-
	Power Dissipation (Max)	60W (Tc)
Operating Temperature 150°C (TJ)	Rds On (Max) @ Id, Vgs	8.1 mOhm @ 38A, 10V
	Operating Temperature	150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package ATPAK	Supplier Device Package	ATPAK
Package / Case ATPAK (2 leads+tab)	Package / Case	ATPAK (2 leads+tab)
Report errors?		Report errors?

#### **ATP214-TL-H Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **ATP214-TL-H Payment Methods**



















### **ATP214-TL-H Shipping Methods**













If you have any question about ATP214-TL-H, please do not hesitate to contact us!

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